

High-Speed Overcurrent Detection

Jaskaran Atwal

Design Goal

OVERCURRENT LEVELS		SUPPLY		TRANSIENT RESPONSE TIME
I_{IN} (min)	I_{IN} (max)	V+	V–	t
0 A	1.0 A	5 V	0 V	< 10 μ s

Design Description

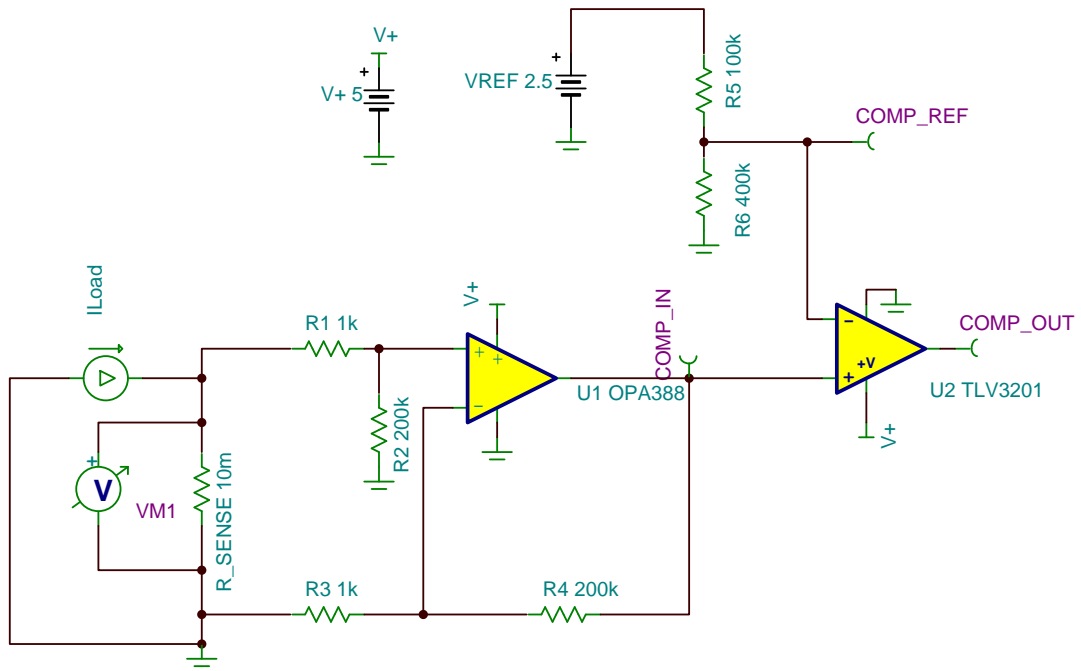
This high-speed, low-side overcurrent detection solution is implemented with a single zero-drift fast-settling amplifier ([OPA388](#)) and one high-speed comparator ([TLV3201](#)). This circuit is designed for applications that monitor fast current signals and overcurrent events, such as current detection in motors and power supply units.

The OPA388 is selected for its widest bandwidth with ultra-low offset and fast slew rate. These parameters allow the circuit to be a well-balanced, high-speed solution in order to accurately detect high frequency current components. In applications that only require average current detection, devices with less bandwidth can be used like the [LPV821](#). In applications that require faster response time, devices with larger bandwidth can be used like the [THS4521](#).

The TLV3201 is selected for its fast response due to its small propagation delay of 40 ns and rise time of 4.8 ns. This allows the comparator to quickly respond and alert the system of an overcurrent event all within the transient response time requirement. The push-pull output stage also allows the comparator to directly interface with the logic levels of the microcontroller. The TLV3201 also has low power consumption with a quiescent current of 40 μ A.

Typically for low-side current detection, the amplifier across the sense resistor can be used in a noninverting configuration. The application circuit shown, however, uses the OPA388 as a differential amplifier across the sense resistor. This provides a true differential measurement across the shunt resistor and can be beneficial in cases where the supply ground and load ground are not necessarily the same.

Dedicated current sense amplifiers can also be an option for high-speed current detection. The tradeoffs for each option should be taken into account when deciding on a current sense solution. Integrated solutions can provide larger bandwidth and savings on board space, but can be more costly and offer limited customization. Discrete solutions can be lower cost and easily customizable, but could require precision resistors to increase measurement precision.



Design Notes

1. To minimize errors, choose precision resistors and set $R_1 = R_3$, and $R_2 = R_4$.
2. Select R_{SENSE} to minimize the voltage drop across the resistor at the max current of 1 A.
3. Due to the ultra-low offset of the OPA388 (0.25 μ V), the effect of any offset error from the amplifier is minimal on the mV range measurement across R_{SENSE} .
4. Select the amplifier gain so COMP_IN reaches 2 V when the system crosses its critical overcurrent value of 1 A.
5. Traditional bypass capacitors are omitted to simplify the application circuit.

Design Steps

1. Determine the transfer equation where $R_1 = R_3$ and $R_2 = R_4$.

$$COMP_IN = (R_{SENSE} \times I_{LOAD}) \times \left(\frac{R_2}{R_1 + R_2} \right) \times \left(1 + \frac{R_4}{R_3} \right) \quad (1)$$

2. Select the SENSE resistor value assuming a maximum voltage drop of 10 mV with a load current of 1 A in order to minimize the voltage drop across the resistor.

$$R_{SENSE} = \frac{V_{SENSE}(\max)}{I_{LOAD}(\text{critical})} = \frac{10 \text{ mV}}{1 \text{ A}} = 10 \text{ m}\Omega \quad (2)$$

3. Select the amplifier gain such that COMP_IN reaches 2 V when the load current reaches the critical threshold of 1 A.

$$Gain = \frac{V_{REF}}{R_{SENSE} \times I_{LOAD}(\text{critical})} = \frac{2 \text{ V}}{.01 \text{ V}} = \frac{R_2}{R_1 + R_2} \times 1 + \frac{R_4}{R_3} = 200 \quad (3)$$

$$\text{Set } R_1 = R_3 = 1 \text{ k}\Omega \quad (4)$$

$$R_2 = R_4 = 200 \text{ k}\Omega \quad (5)$$

4. Calculate the transimpedance gain of the amplifier in order to verify the AC simulation results shown below.

$$V_{OUT} = I_{LOAD} \times 10 \text{ m}\Omega \times 200 \quad (6)$$

$$\frac{V_{OUT}}{I_{LOAD}} = 10 \text{ m}\Omega \times 200 = 2 \quad (7)$$

Design Simulations

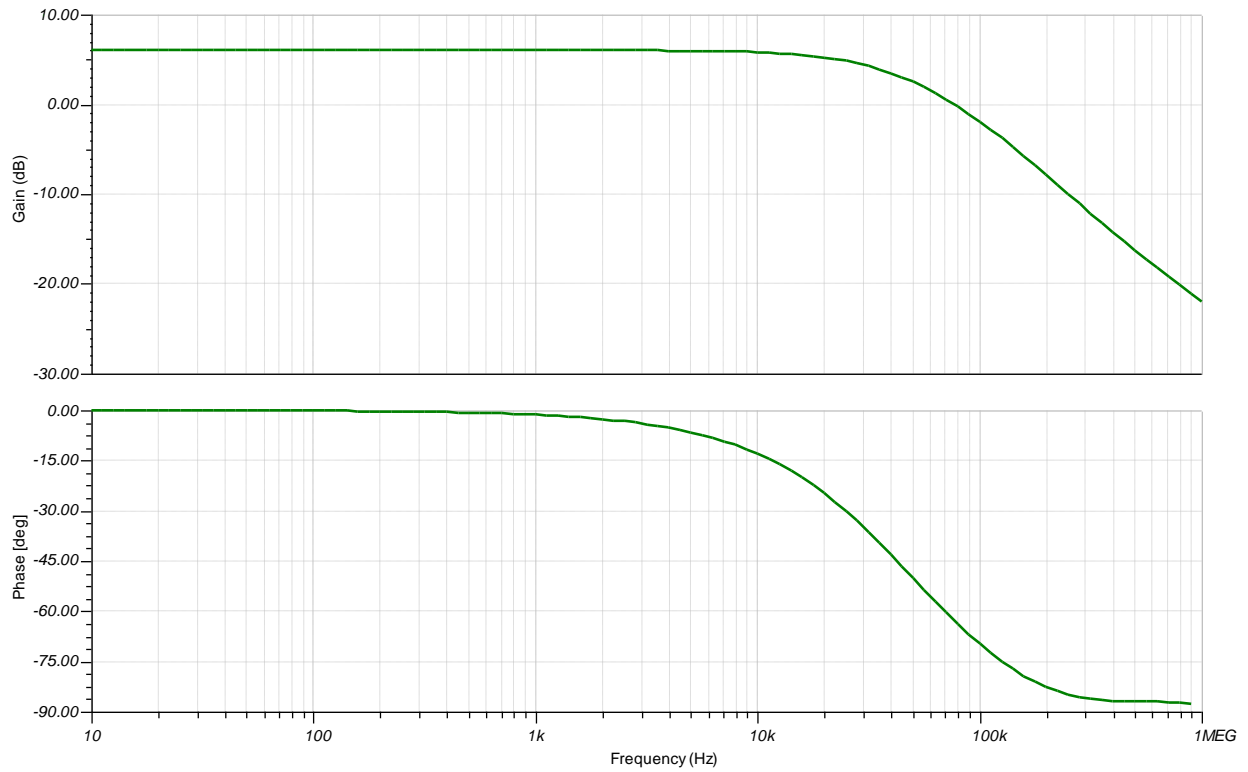


Figure 1. COMP_IN Transimpedance AC Simulation Results

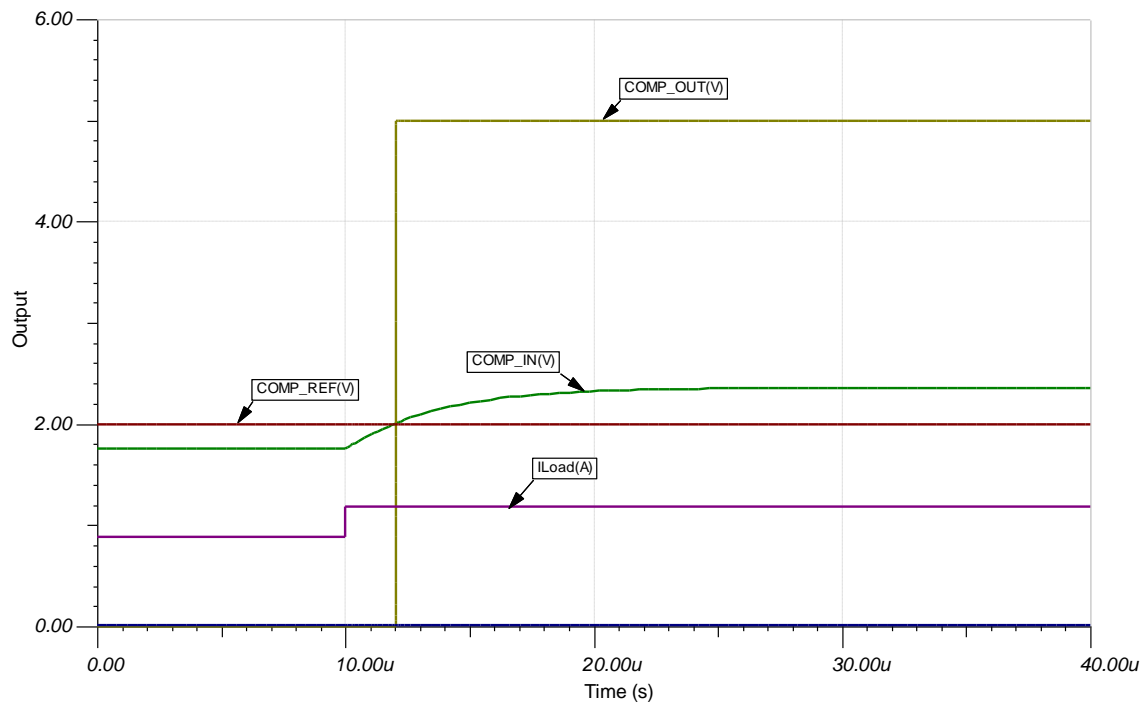


Figure 2. Transient Response Simulation Results

Tech Note and Blog References

See [Advantages of using Nanopower Zero Drift Amp for Mobile Phone Battery Monitoring](#) (SNOA977).

See [Current Sensing in No-Neutral Light Switches](#) (SNOA968).

See [GPIO Pins Power Signal Chain in Personal Electronics Running on Li-Ion Batteries](#) (SNOA983).

See the [Current Sensing Using NanoPower Op Amps](#) blog.

Table 1. Design Featured Comparator

TLV3201	
V_S	2.7 V to 5.5 V
t_{PD}	40 ns
Input V_{CM}	Rail-to-rail
V_{os}	1 mV
I_q	40 μ A
TLV3201	

Table 2. Design Alternate Comparator

TLV7021	
V_S	1.6 V to 5.5 V
t_{PD}	260 ns
Input V_{CM}	Rail-to-rail
V_{os}	0.5 mV
I_q	5 μ A
TLV7021	

Table 3. Design Featured Op Amp

OPA388	
V_S	2.5 V to 5.5 V
Input V_{CM}	Rail-to-rail
V_{out}	Rail-to-rail
V_{os}	0.25 μ V
V_{os} Drift	.005 μ V/ $^{\circ}$ C
I_q	1.7 mA/Ch
I_b	30 pA
UGBW	10 MHz
OPA388	

Table 4. Design Alternate Op Amp

THS4521	
V_S	2.5 V to 5.5 V
Input V_{CM}	Rail-to-rail
V_{out}	Rail-to-rail
V_{os}	200 μ V
V_{os} Drift	2 μ V/ $^{\circ}$ C
I_q	1 mA/Ch
I_b	0.65 μ A
UGBW	145 MHz
THS4521	

IMPORTANT NOTICE FOR TI DESIGN INFORMATION AND RESOURCES

Texas Instruments Incorporated ("TI") technical, application or other design advice, services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using any particular TI Resource in any way, you (individually or, if you are acting on behalf of a company, your company) agree to use it solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources.

You understand and agree that you remain responsible for using your independent analysis, evaluation and judgment in designing your applications and that you have full and exclusive responsibility to assure the safety of your applications and compliance of your applications (and of all TI products used in or for your applications) with all applicable regulations, laws and other applicable requirements. You represent that, with respect to your applications, you have all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. You agree that prior to using or distributing any applications that include TI products, you will thoroughly test such applications and the functionality of such TI products as used in such applications. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

You are authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING TI RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY YOU AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

You agree to fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of your non-compliance with the terms and provisions of this Notice.

This Notice applies to TI Resources. Additional terms apply to the use and purchase of certain types of materials, TI products and services. These include; without limitation, TI's standard terms for semiconductor products (<http://www.ti.com/sc/docs/stdterms.htm>), [evaluation modules](#), and [samples](http://www.ti.com/sc/docs/sampterm.htm) (<http://www.ti.com/sc/docs/sampterm.htm>).

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2018, Texas Instruments Incorporated